

FQT1N60C

N-Channel QFET® MOSFET 600V, 0.2 A, 11.5 Ω

Description

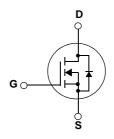
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



Features

- 0.2 A, 600 V, $R_{DS(on)}$ =9.3 $\Omega(V^{\hat{}}]$.)@ V_{GS} =10 V, I_D =0.1 A
- Low Gate Charge (Typ. I È nC)
- Low C_{rss} (Typ. HĚ pF)
- 100% Avalanche Tested
- RoHS Compliant





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol		Parameter		FQT1N60C	Unit
V _{DSS}	Drain to Source Voltage			600	V
V _{GSS}	Gate to Source Voltage			±30	V
	Drain Current	-Continuous (T _C = 25°C)		0.2	А
ID	Diamounent	-Continuous (T _C = 100°C)		0.12	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	0.8	Α
E _{AS}	Single Pulsed Avalanche E	nergy	(Note 2)	33	mJ
I _{AR}	Avalanche Current		(Note 1)	0.2	Α
E _{AR}	Repetitive Avalanche Energ	gy	(Note 1)	0.2	mJ
dv/dt	Peak Diode Recovery dv/d	t	(Note 3)	4.5	V/ns
n	Dawer Discinction	(T _C = 25°C)		2.1	W
P_{D}	Power Dissipation	- Derate above 25°C		0.02	W/°C
T _J , T _{STG}	Operating and Storage Ten	nperature Range		-55 to +150	°C
T _L	•	Maximum Lead Temperature for Soldering Purpose, /8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Min.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient*		60	°C/W

^{*} When mounted on the minimum pad size recommended (PCB Mount)

Package Marking and Ordering Information T_C = 25°C unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQT1N60C	FQT1N60C	SOT-223	330mm	12mm	4000

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A$, $V_{GS} = 0V$, $T_J = 25^{\circ}C$	600	-	-	V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.6	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	-	-	25	μА
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 480V, T_{C} = 125^{\circ}C$	-	-	250	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.0	-	4.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 0.1A$	-	9.3	11.5	Ω
g _{FS}	Forward Transconductance	$V_{DS} = 40V, I_D = 0.1A$ (Note 4)	-	0.75	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	051/1/ 01/		-	130	170	pF
C _{oss}	Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz		-	19	25	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1101112		-	3.5	6	pF
Q_g	Total Gate Charge at 10V			-	4.8	6.2	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 480V, I_{D} = 1A$		-	0.7	-	nC
Q _{gd}	Gate to Drain "Miller" Charge	V _{GS} = 10V	(Note 4, 5)	-	2.7	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	7	24	ns
t _r	Turn-On Rise Time	$V_{DD} = 300V, I_{D} = 1A$	-	21	52	ns
t _{d(off)}	Turn-Off Delay Time	$R_G = 25\Omega$	-	13	36	ns
t _f	Turn-Off Fall Time	(Note 4, 5)	-	27	64	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current			-	0.2	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	0.8	Α
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{SD} = 0.2A$	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 1A	-	190	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$ (No	te 4) -	0.53	-	μС

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 59mH, I $_{AS}$ = 1.1A, V $_{DD}$ = 50V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C
- 3. $I_{SD} \le 0.2 A, \ di/dt \le 200 A/\mu s, \ V_{DD} \le BV_{DSS}, \ Starting \ T_J$ = 25°C
- 4. Pulse Test: Pulse width $\leq 300 \mu s, \, \text{Duty Cycle} \leq 2\%$
- 5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

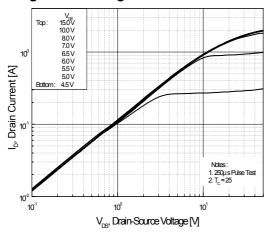


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

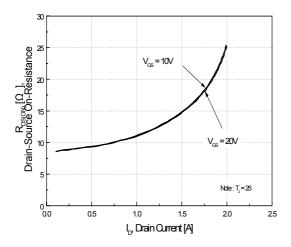


Figure 5. Capacitance Characteristics

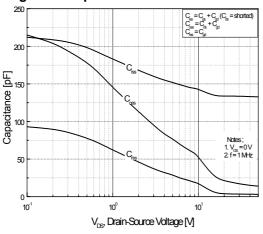


Figure 2. Transfer Characteristics

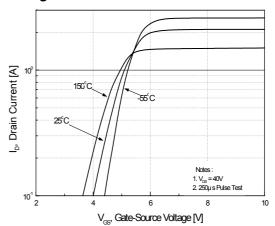


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

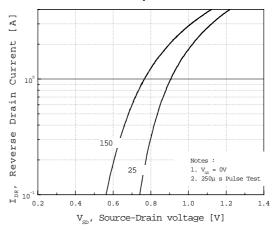
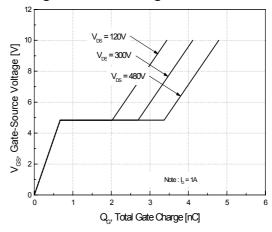


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

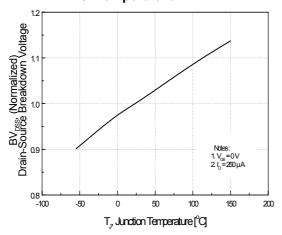


Figure 8. On-Resistance Variation vs. Temperature

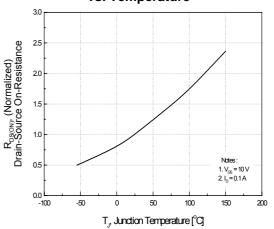


Figure 9. Maximum Safe Operating Area

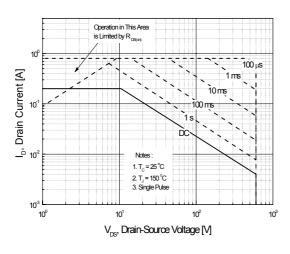


Figure 10. Maximum Drain Current vs. Case Temperature

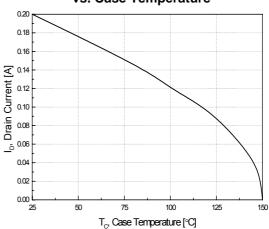
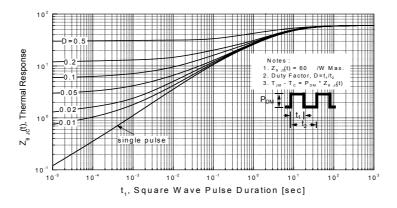
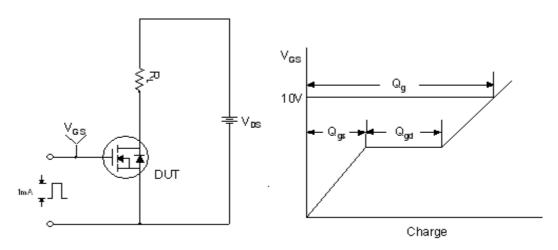


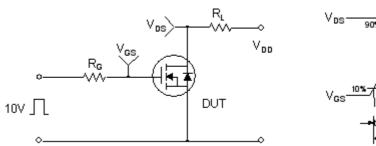
Figure 11. Transient Thermal Response Curve

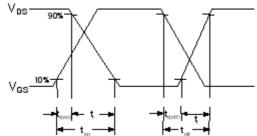


Gate Charge Test Circuit & Waveform

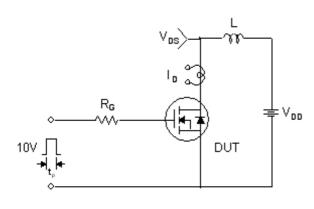


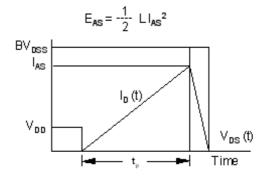
Resistive Switching Test Circuit & Waveforms



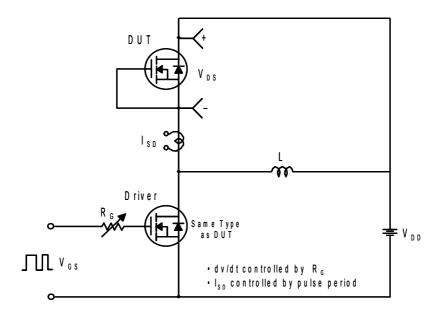


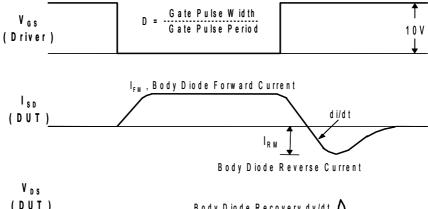
Unclamped Inductive Switching Test Circuit & Waveforms

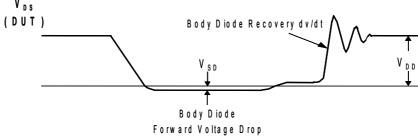




Peak Diode Recovery dv/dt Test Circuit & Waveforms

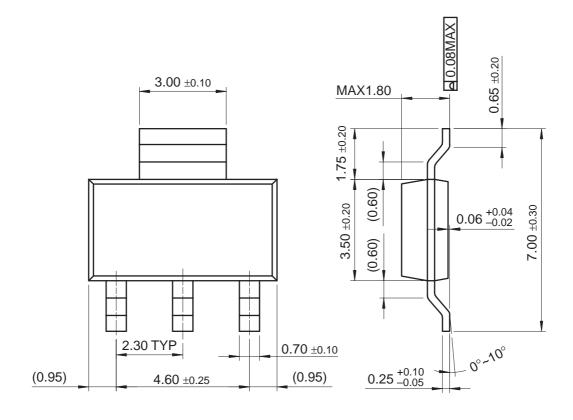


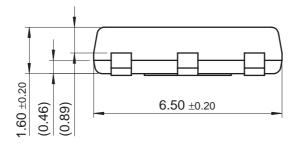




Mechanical Dimensions

SOT-223









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Rev. 164